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Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS

DATA SHEET



BAS45ALow-leakage diode

Product data sheet Supersedes data of June 1994 1996 Mar 13



Low-leakage diode

BAS45A

FEATURES

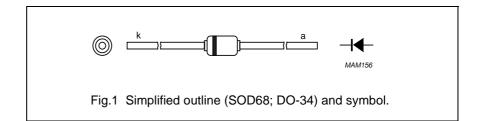
- Continuous reverse voltage: max. 125 V
- Repetitive peak forward current: max. 625 mA
- Low reverse current: max. 1 nA
- Switching time: typ. 1.5 μs.

APPLICATION

· Low leakage current applications.

DESCRIPTION

Epitaxial medium-speed switching diode with a low leakage current in a hermetically-sealed glass SOD68 (DO-34) package.



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{RRM}	repetitive peak reverse voltage		_	125	V
V _R	continuous reverse voltage		=	125	V
I _F	continuous forward current	see Fig.2; note 1	_	250	mA
I _{FRM}	repetitive peak forward current		_	625	mA
I _{FSM}	non-repetitive peak forward current	square wave; T _j = 25 °C prior to surge; see Fig.4			
		t _p = 1 μs	_	4	Α
		$t_p = 1 \text{ ms}$	_	1	Α
		t _p = 1 s	_	0.5	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	=	300	mW
T _{stg}	storage temperature		-65	+175	°C
Tj	junction temperature		_	175	°C

Note

1. Device mounted on a printed-circuit board without metallization pad.

Low-leakage diode

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ELECTRICAL CHARACTERISTICS

 $T_j = 25$ °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V _F	forward voltage	see Fig.3			
		I _F = 1 mA	_	780	mV
		I _F = 10 mA	_	860	mV
		I _F = 100 mA	_	1000	mV
I_R	reverse current	see Fig.5			
		$V_R = 125 \text{ V}; E_{max} = 100 \text{ Ix}$	_	1	nA
		$V_R = 30 \text{ V}; T_j = 125 \text{ °C}; E_{max} = 100 \text{ lx}$	_	300	nA
		$V_R = 125 \text{ V}; T_j = 125 \text{ °C}; E_{max} = 100 \text{ Ix}$	_	500	nA
		$V_R = 125 \text{ V}; T_j = 150 \text{ °C}; E_{max} = 100 \text{ lx}$	_	2	μΑ
C_d	diode capacitance	f = 1 MHz; V _R = 0; see Fig.6	_	4	pF
t _{rr}	reverse recovery time	when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω ; measured at I_R = 1 mA; see Fig.7	1.5	_	μs

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-tp}	thermal resistance from junction to tie-point	8 mm from the body	300	K/W
R _{th j-a}	thermal resistance from junction to ambient	lead length 10 mm; note 1	500	K/W

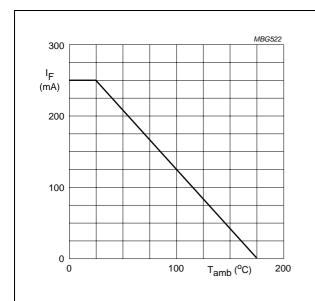
Note

1. Device mounted on a printed-circuit board without metallization pad.

Low-leakage diode

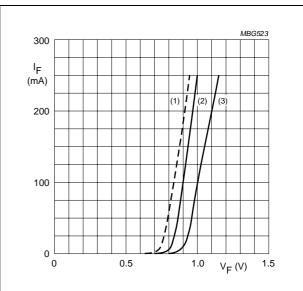
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GRAPHICAL DATA



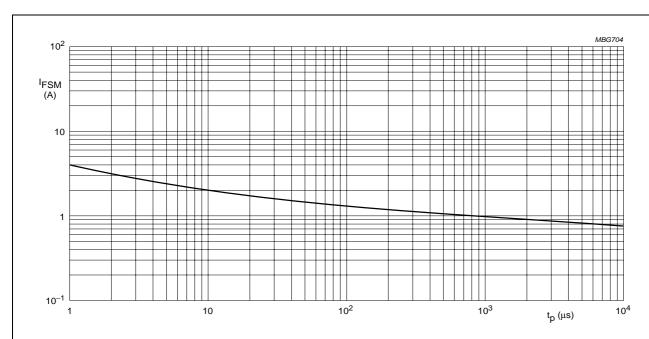
Device mounted on a printed-circuit board without metallization pad.

Fig.2 Maximum permissible continuous forward current as a function of ambient temperature.



- (1) $T_j = 150$ °C; typical values.
- (2) $T_j = 25 \,^{\circ}\text{C}$; typical values.
- (3) $T_j = 25$ °C; maximum values.

Fig.3 Forward current as a function of forward voltage.

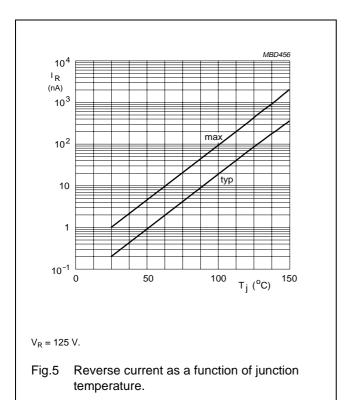


Based on square wave currents; $T_j = 25$ °C prior to surge.

Fig.4 Maximum permissible non-repetitive peak forward current as a function of pulse duration.

Low-leakage diode

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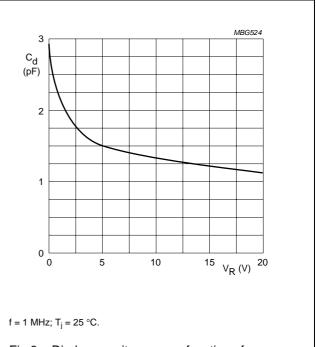
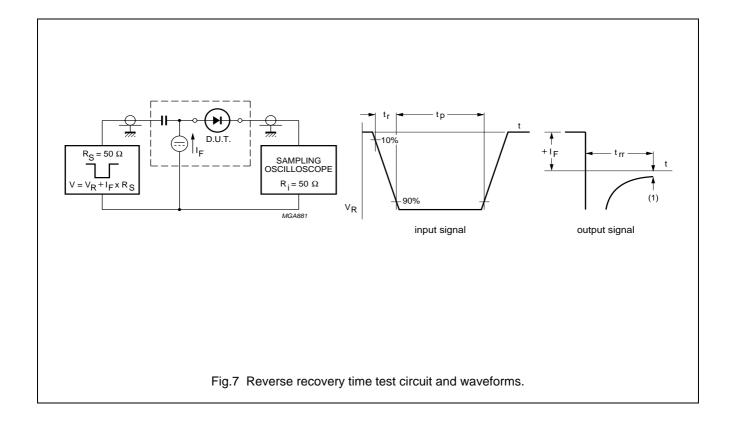


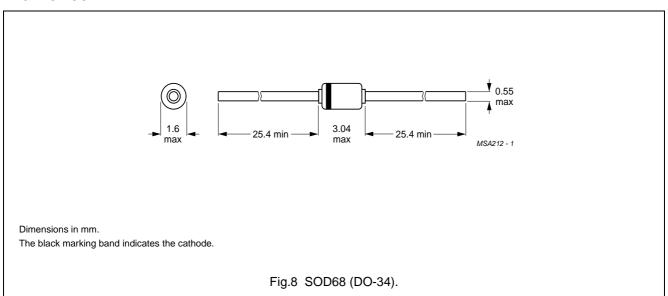
Fig.6 Diode capacitance as a function of reverse voltage; typical values.



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PACKAGE OUTLINE



Low-leakage diode

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DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
- 2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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